

## Advanced Power MOSFET

## SSW/I2N80A

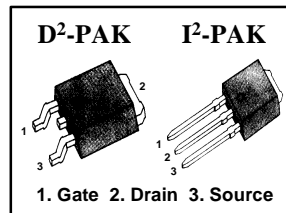
## FEATURES

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 25  $\mu$ A (Max.) @  $V_{DS} = 800V$
- Low  $R_{DS(ON)}$  : 4.688  $\Omega$  (Typ.)

$$BV_{DSS} = 800 V$$

$$R_{DS(on)} = 6.0 \Omega$$

$$I_D = 2 A$$



## Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	800	V
$I_D$	Continuous Drain Current ( $T_C=25^\circ C$ )	2	A
	Continuous Drain Current ( $T_C=100^\circ C$ )	1.3	
$I_{DM}$	Drain Current-Pulsed ①	8	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy ②	213	mJ
$I_{AR}$	Avalanche Current ①	2	A
$E_{AR}$	Repetitive Avalanche Energy ①	8	mJ
dv/dt	Peak Diode Recovery dv/dt ③	2.0	V/ns
$P_D$	Total Power Dissipation ( $T_C=25^\circ C$ )	3.1	W
	Linear Derating Factor	80	
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	0.64	$^\circ C$
		- 55 to +150	
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

## Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	1.56	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient *	--	40	
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

\* When mounted on the minimum pad size recommended (PCB Mount).

Rev. B

**Electrical Characteristics** ( $T_C=25^\circ\text{C}$  unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$BV_{DSS}$	Drain-Source Breakdown Voltage	800	--	--	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	1.06	--	V/°C	$I_D=250\mu A$ <b>See Fig 7</b>
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	3.5	V	$V_{DS}=5V, I_D=250\mu A$
$I_{GSS}$	Gate-Source Leakage, Forward	--	--	100	nA	$V_{GS}=30V$
	Gate-Source Leakage, Reverse	--	--	-100		$V_{GS}=-30V$
$I_{DSS}$	Drain-to-Source Leakage Current	--	--	25	$\mu A$	$V_{DS}=800V$
		--	--	250		$V_{DS}=640V, T_C=125^\circ C$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	6.0	$\Omega$	$V_{GS}=10V, I_D=0.85A$ ④*
$g_{fs}$	Forward Transconductance	--	1.56	--	$\Omega$	$V_{DS}=50V, I_D=0.85A$ ④
$C_{iss}$	Input Capacitance	--	425	550	pF	$V_{GS}=0V, V_{DS}=25V, f=1MHz$ <b>See Fig 5</b>
$C_{oss}$	Output Capacitance	--	45	55		
$C_{rss}$	Reverse Transfer Capacitance	--	19	25		
$t_{d(on)}$	Turn-On Delay Time	--	15	40	ns	$V_{DD}=400V, I_D=2A,$ $R_G=16\Omega$ <b>See Fig 13</b> ④ ⑤
$t_r$	Rise Time	--	22	55		
$t_{d(off)}$	Turn-Off Delay Time	--	38	85		
$t_f$	Fall Time	--	18	45		
$Q_g$	Total Gate Charge	--	22	30	nC	$V_{DS}=640V, V_{GS}=10V,$ $I_D=2A$ <b>See Fig 6 &amp; Fig 12</b> ④ ⑤
$Q_{gs}$	Gate-Source Charge	--	3.8	--		
$Q_{gd}$	Gate-Drain("Miller") Charge	--	11.6	--		

**Source-Drain Diode Ratings and Characteristics**

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$I_S$	Continuous Source Current	--	--	2	A	Integral reverse pn-diode in the MOSFET
$I_{SM}$	Pulsed-Source Current ①	--	--	8		
$V_{SD}$	Diode Forward Voltage ④	--	--	1.4	V	$T_J=25^\circ C, I_S=1.7A, V_{GS}=0V$
$t_{rr}$	Reverse Recovery Time	--	290	--	ns	$T_J=25^\circ C, I_F=2A$
$Q_{rr}$	Reverse Recovery Charge	--	0.8	--	$\mu C$	$di_F/dt=100A/\mu s$ ④

**Notes ;**

① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature

②  $L=100mH, I_{AS}=2A, V_{DD}=50V, R_G=27\Omega,$  Starting  $T_J=25^\circ C$ ③  $I_{SD}\leq 2A, di/dt\leq 90A/\mu s, V_{DD}\leq BV_{DSS},$  Starting  $T_J=25^\circ C$ ④ Pulse Test : Pulse Width = 250  $\mu s,$  Duty Cycle  $\leq 2\%$ 

⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

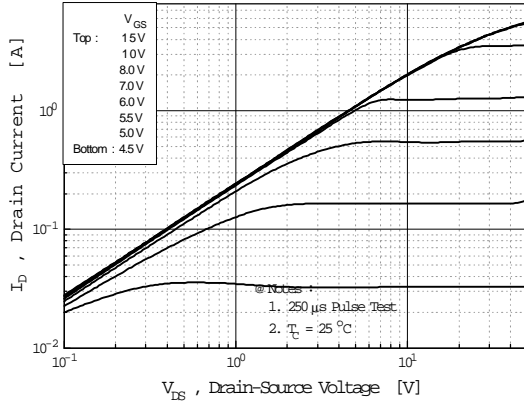


Fig 2. Transfer Characteristics

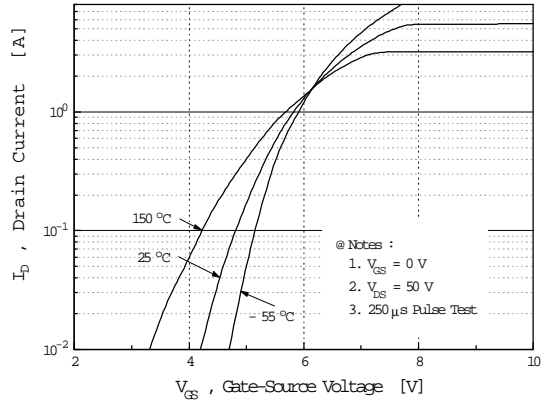


Fig 3. On-Resistance vs. Drain Current

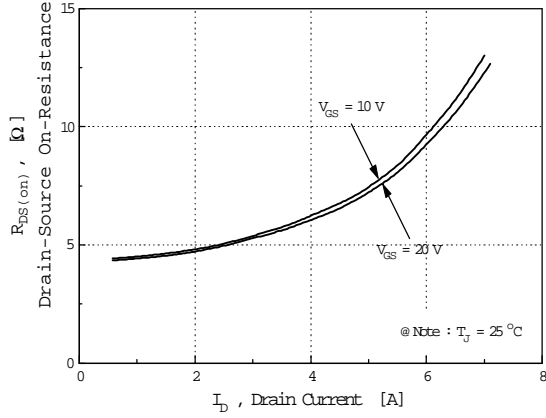


Fig 4. Source-Drain Diode Forward Voltage

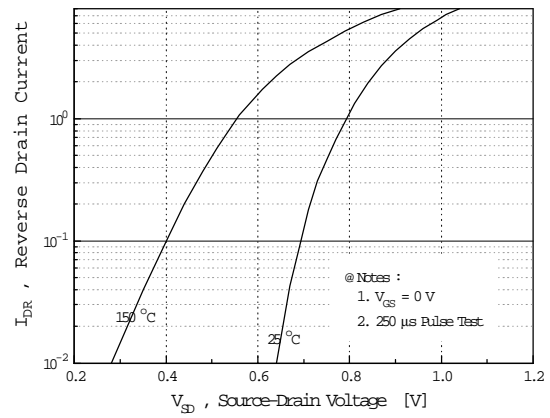


Fig 5. Capacitance vs. Drain-Source Voltage

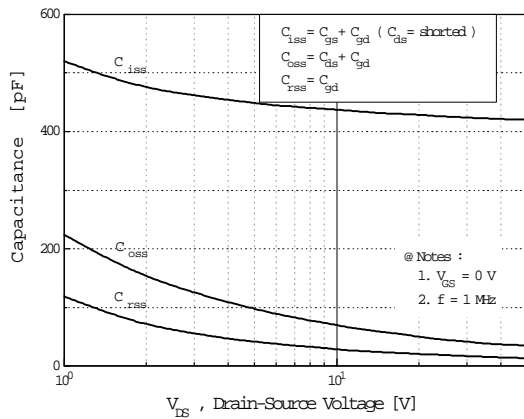
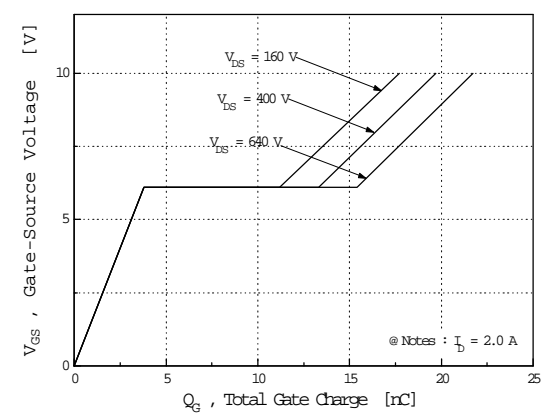


Fig 6. Gate Charge vs. Gate-Source Voltage



# SSW/I2N80A

# N-CHANNEL POWER MOSFET

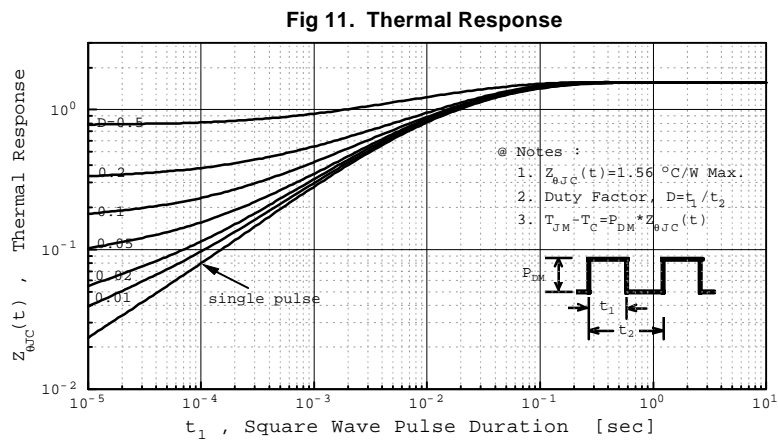
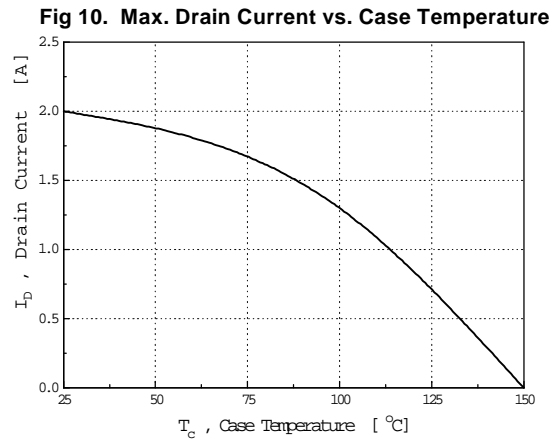
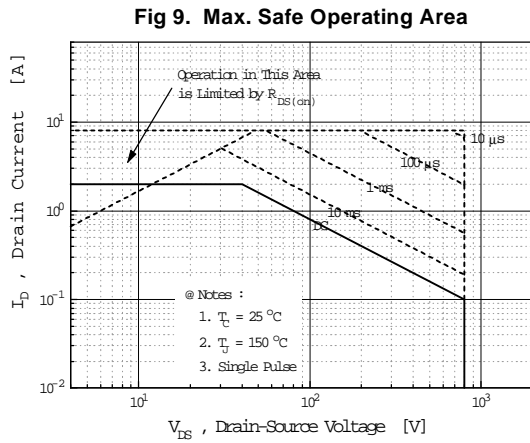
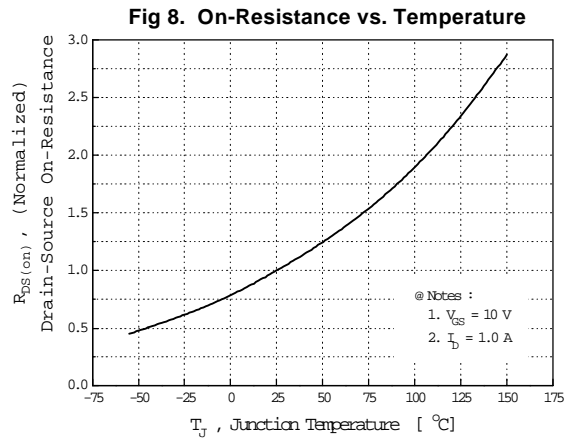
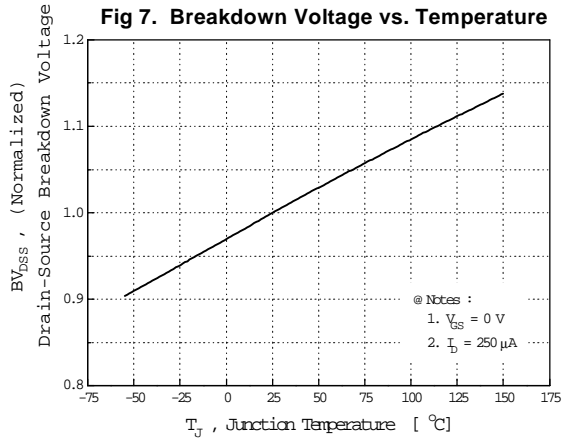


Fig 12. Gate Charge Test Circuit & Waveform

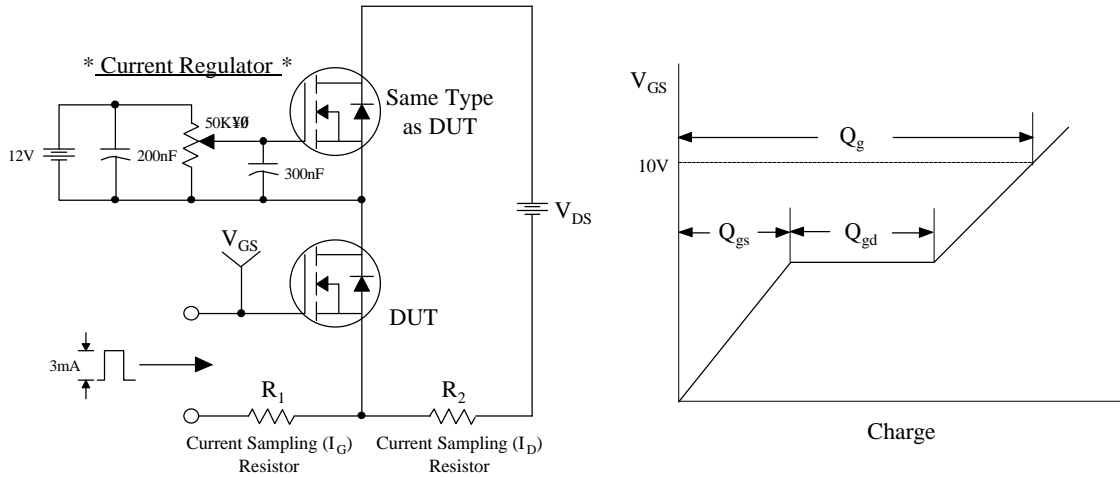


Fig 13. Resistive Switching Test Circuit & Waveforms

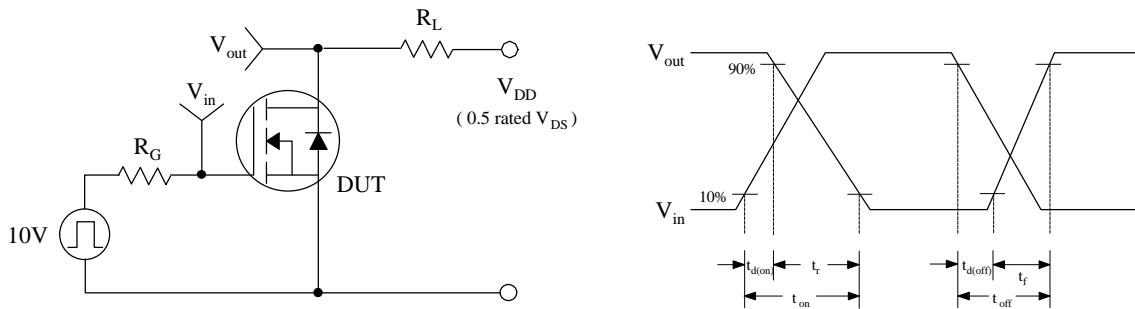


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

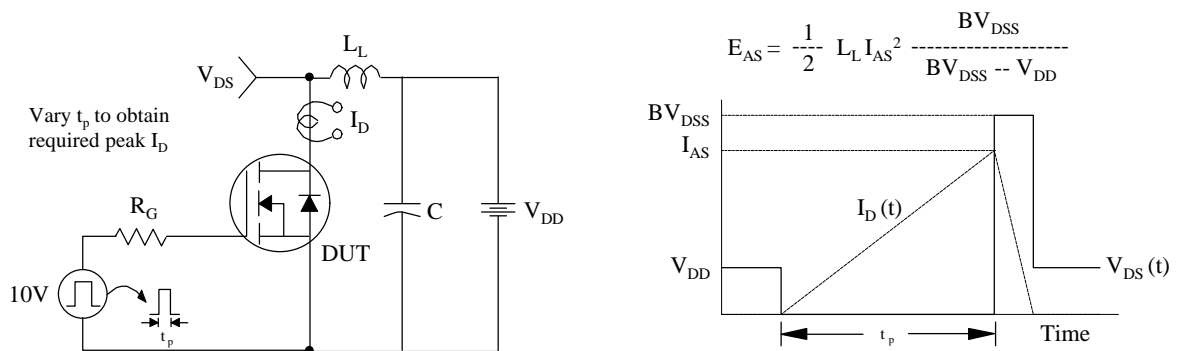
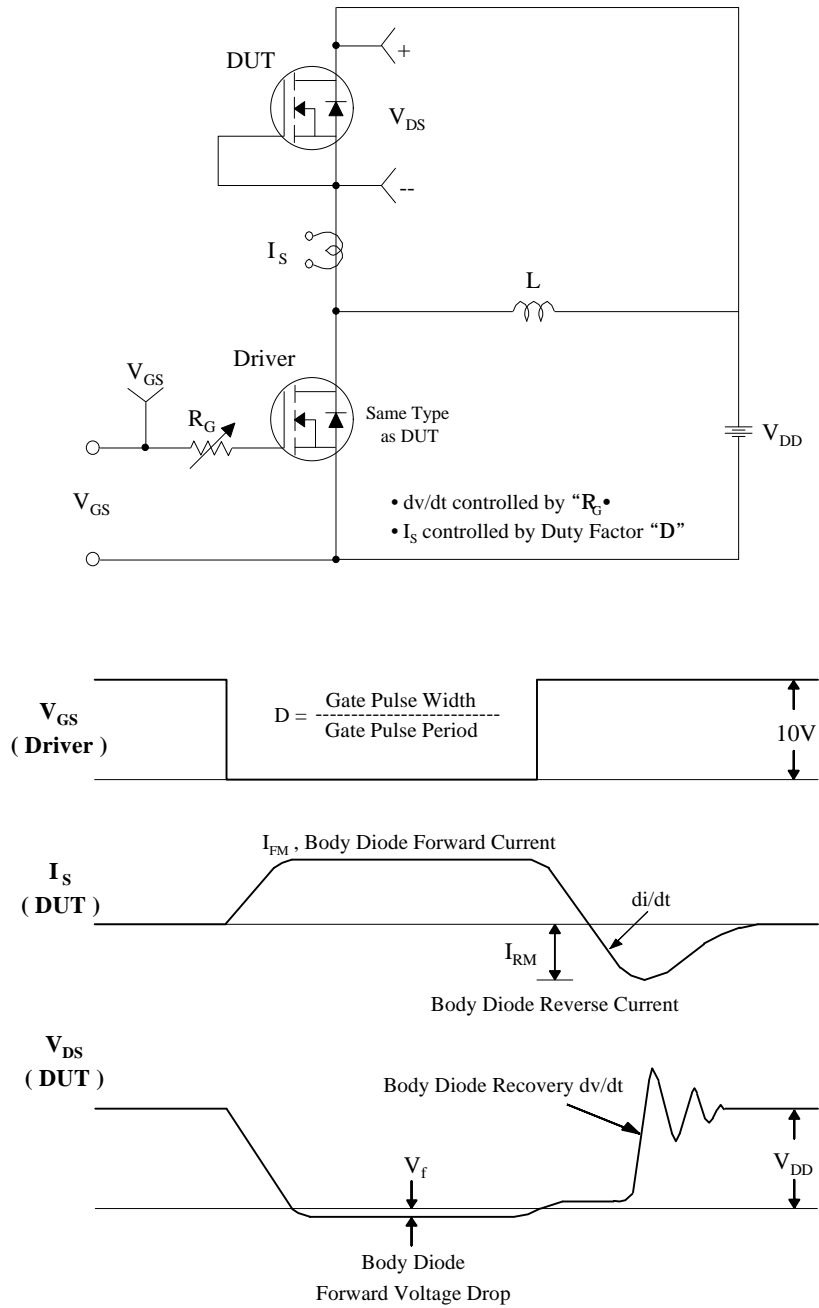


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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